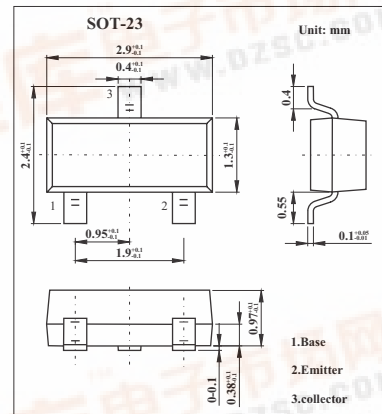


SMD Type Transistors

High Voltage High Performance Transistor
FMMT497

■ Features

- SOT23 NPN silicon planar



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	300	V
Collector-emitter voltage	V _{CEO}	300	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	500	mA
Peak collector current	I _{CM}	1	A
Base current	I _B	200	mA
Power dissipation	P _{tot}	500	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA	300			V
Collector-emitter breakdown voltage *	V _{(BR)CEO}	I _C =10mA	300			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA	5			V
Collector cutoff current	I _{CBO}	V _{CB} =250V			100	nA
Collector Cut-Off Current	I _{CES}	V _{CE} =250V			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V			100	nA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =100mA, I _B =10mA I _C =250mA, I _B =25mA			0.2 0.3	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =250mA, I _B =25mA			1.0	V
Base-emitter voltage *	V _{BE(ON)}	I _C =250mA, V _{CE} =10V			1.0	V
Static Forward Current Transfer Ratio	h _{FE}	I _C =1mA, V _{CE} =10V	100			
		I _C =100mA, V _{CE} =10V*	80		300	
		I _C =250mA, V _{CE} =10V*	20			
Transition Frequency	f _T	I _C =50mA, V _{CE} =10V, f=100MHz	75			MHz
Collector-Base Breakdown Voltage	C _{obo}	V _{CB} =10V, f=1MHz			5	pF

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

497

